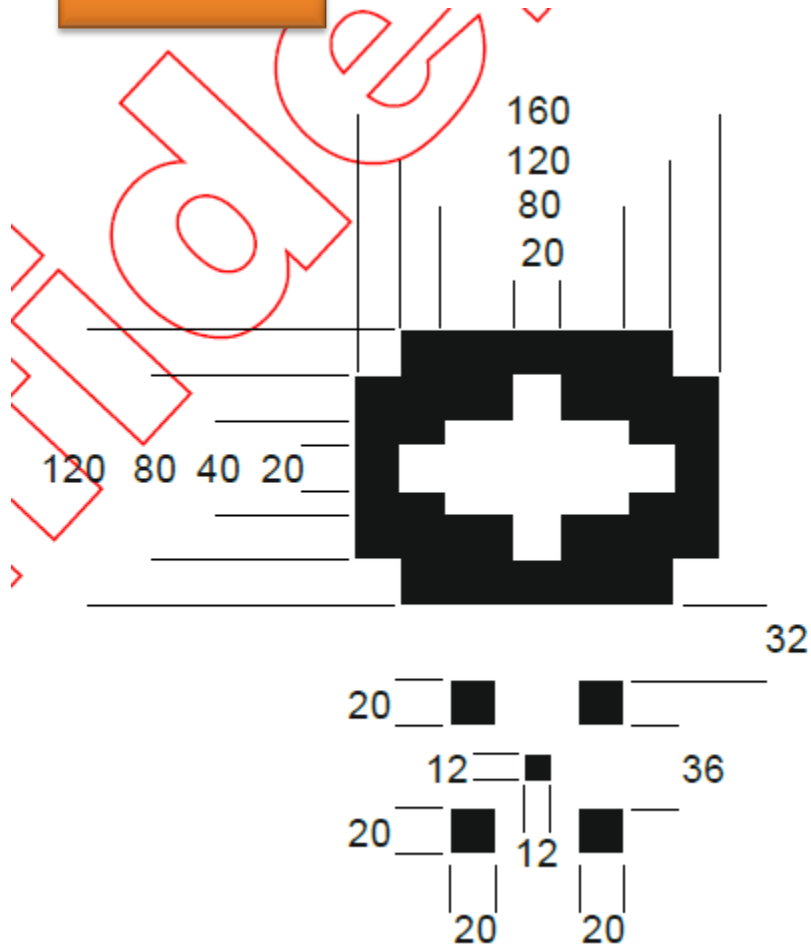


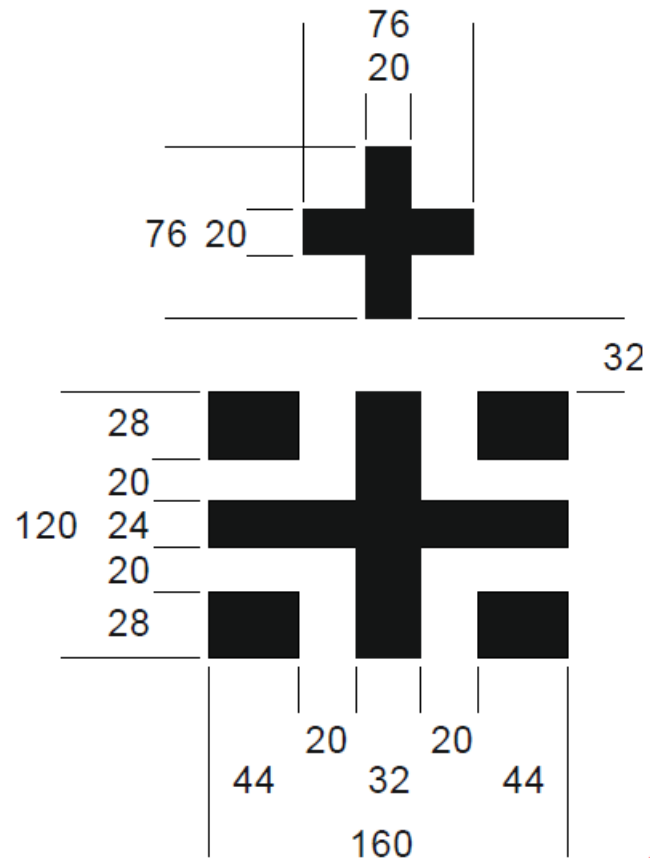
Dimensions of alignment marks

On mask

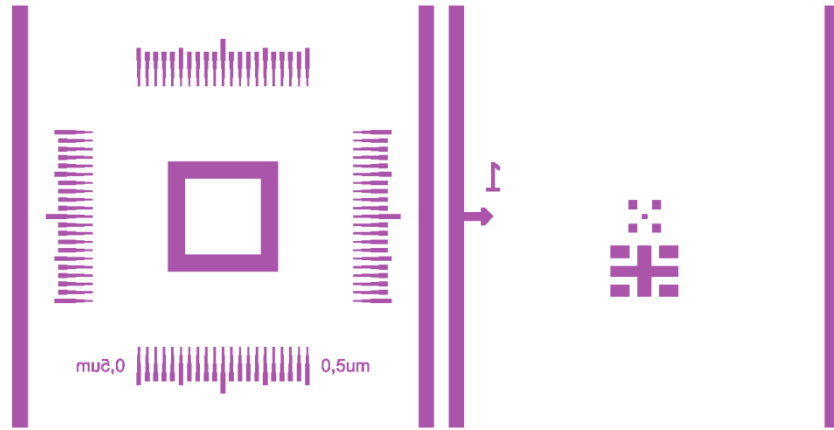


On substrate

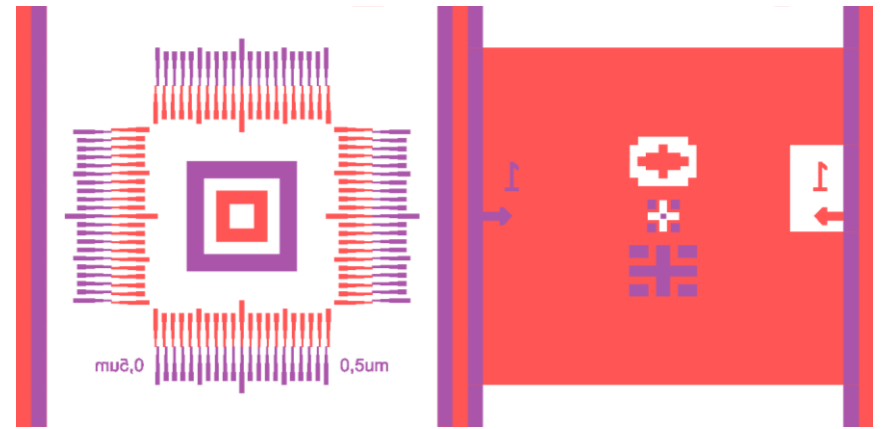
Unit: μm



Alignment



Mark on mask

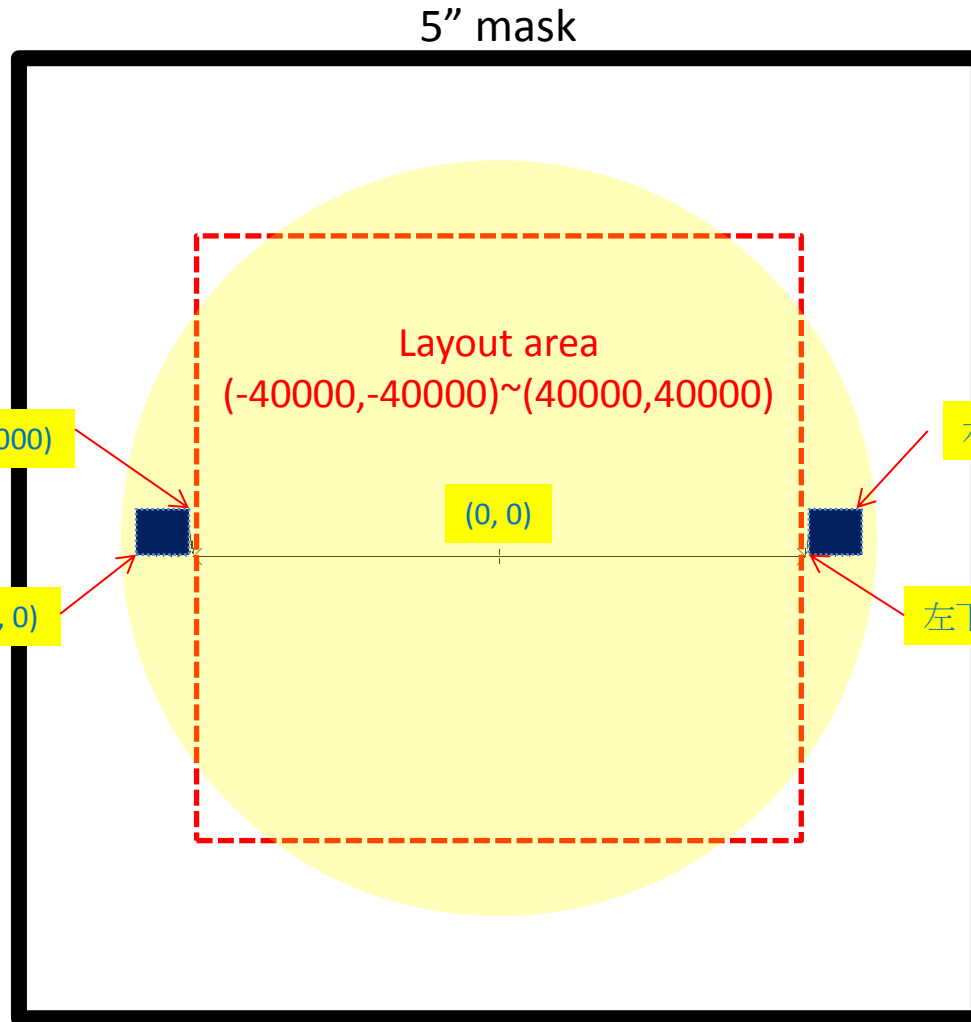


Mark aligned OK



Mark on substrate

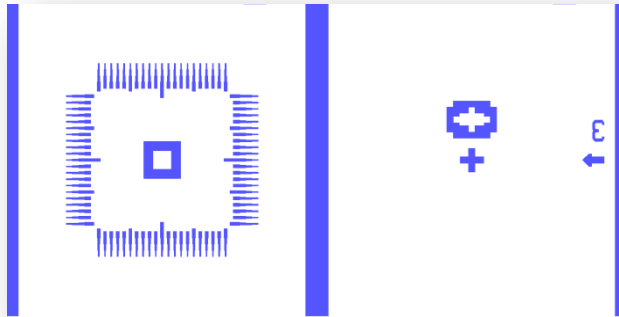
STD alignment marks on 5" mask (for 4" 6" 8" wafer TSA/BSA)



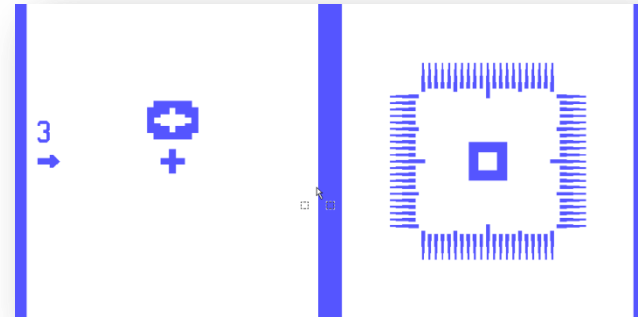
左、右藍色區塊為對準標記區域以及座標，對準標記由TSRI套製，繪圖時請勿占用。

Layout area
(-40000,-40000)~(40000,40000)
為使用者繪圖區，區域內由使用者自行繪製勿超界，晶圓上實際可曝光區域為直徑100mm圓。

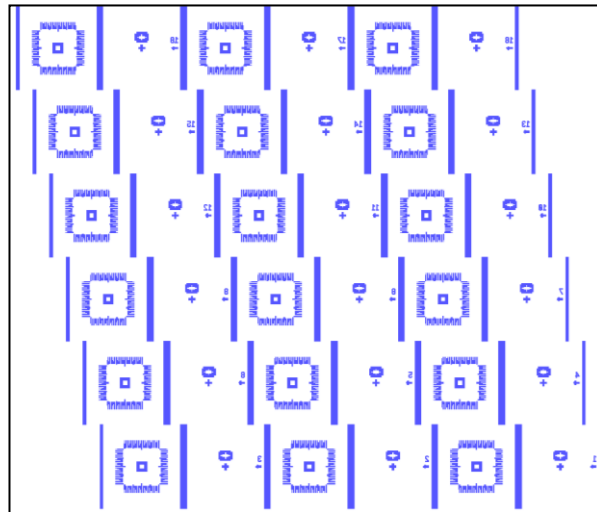
STD zeromark details(total 18 sets)



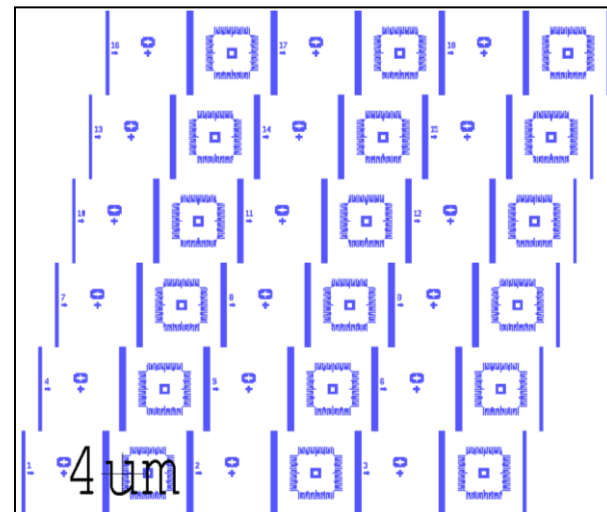
mark L3



mark R3



Left mark group



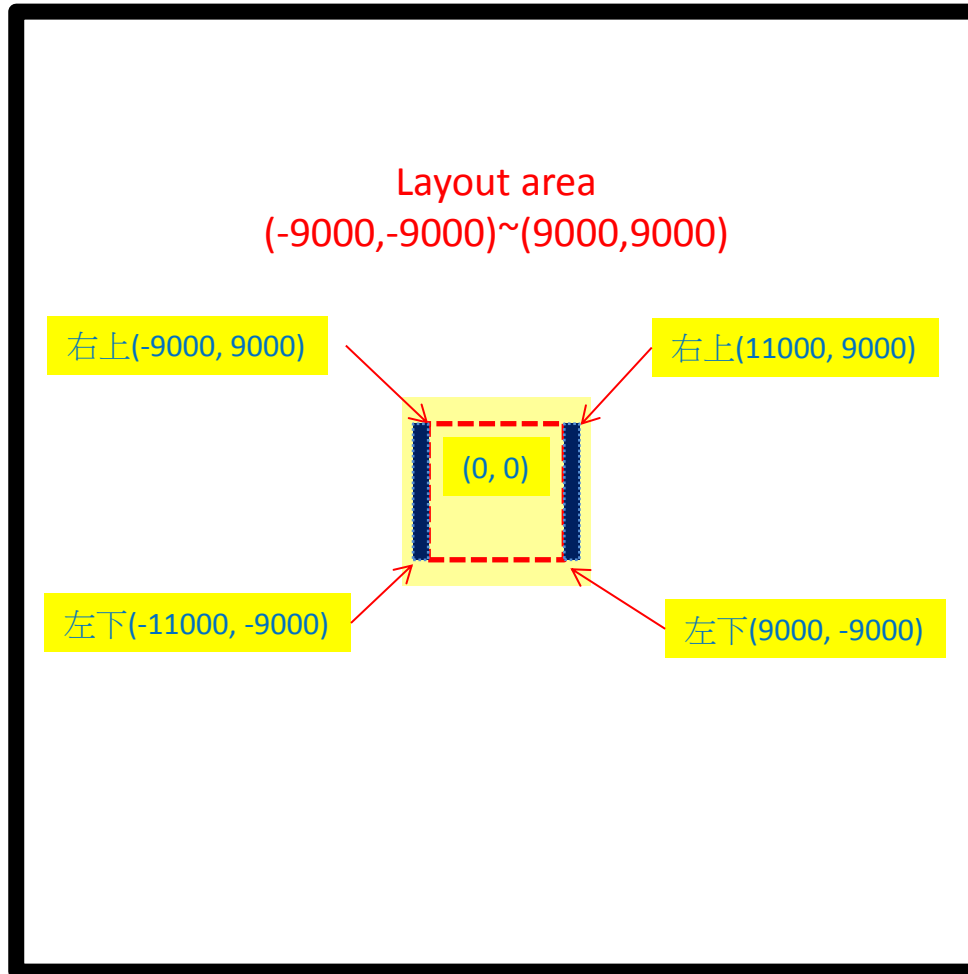
Right mark group

R18 R17 R16
.
.
.
... L4
L3 L2 L1

R16 R17 R18
.
.
.
R4...
R1 R2 R3

STD alignment marks on 5" mask (for 25mm chip TSA)

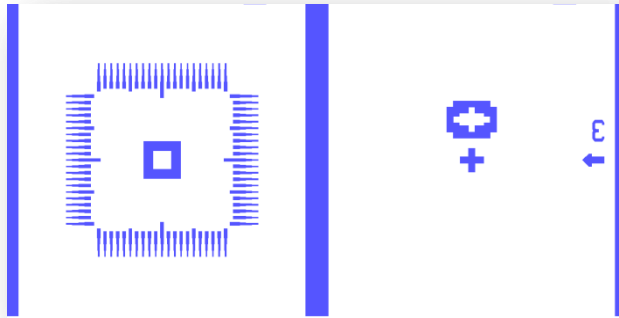
5" mask



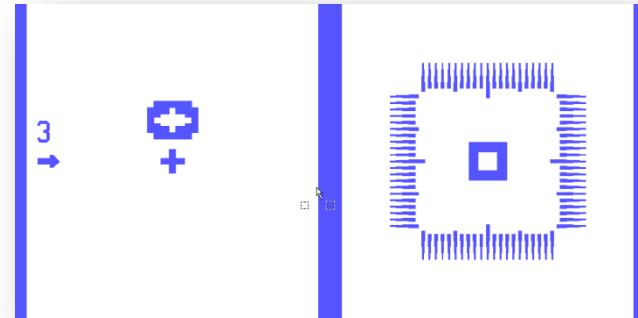
左、右藍色區塊為對準標記區域以及座標，繪圖時請勿占用，

Layout area (-9000,-9000)~(9000,9000)為使用者繪圖區，區域內由使用者自行繪製勿超界，對準標記由TSRI套製。

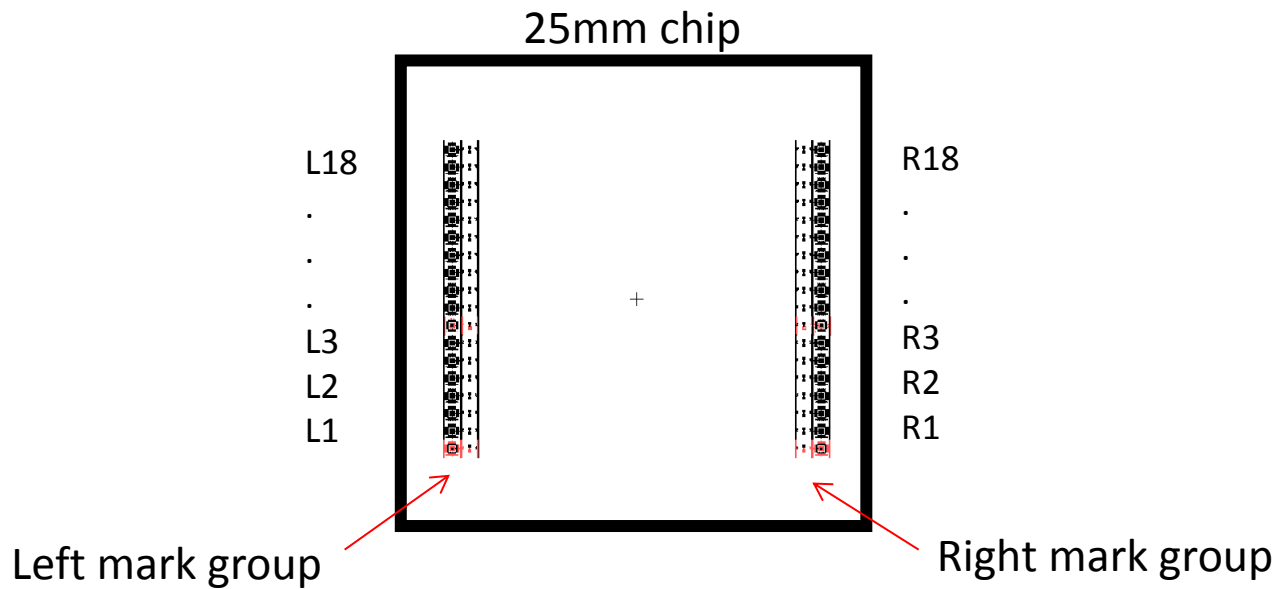
STD zeromark details(total 18 sets)



mark L3

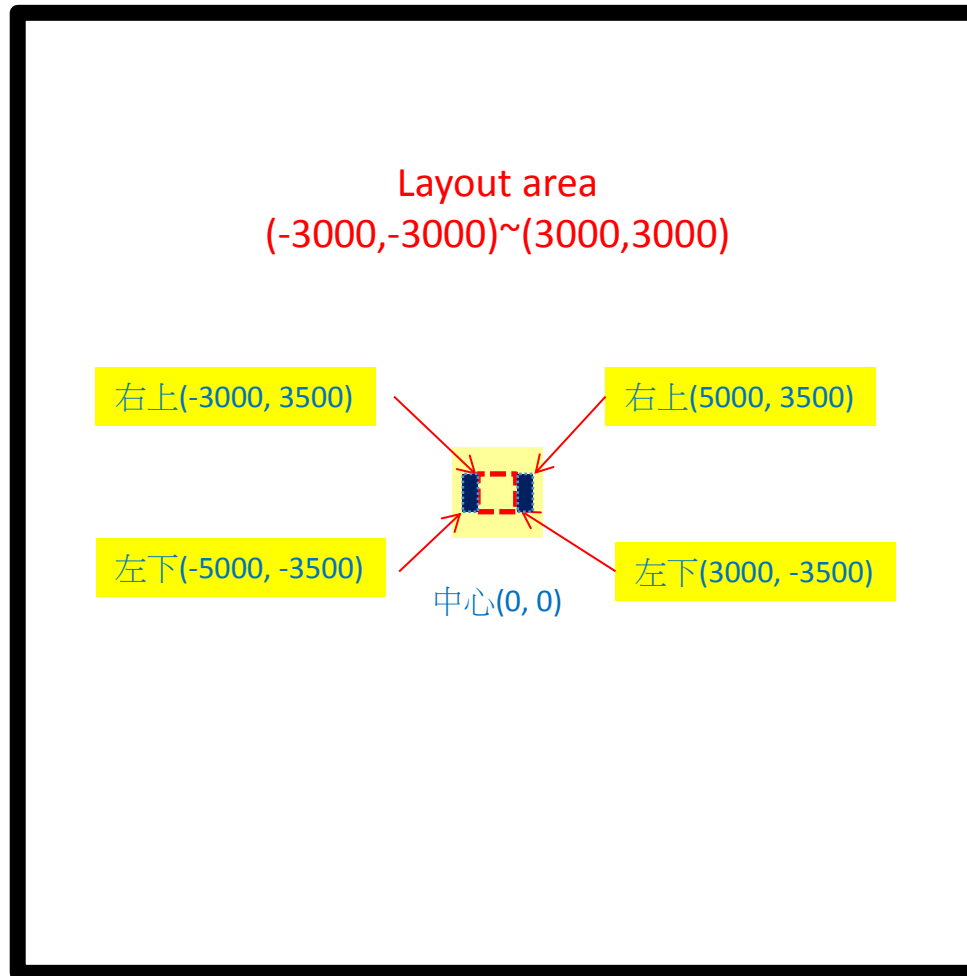


mark R3



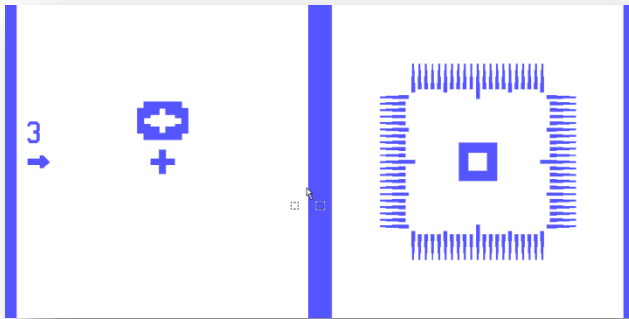
STD alignment marks on 5" mask (for 12mm chip TSA)

5" mask

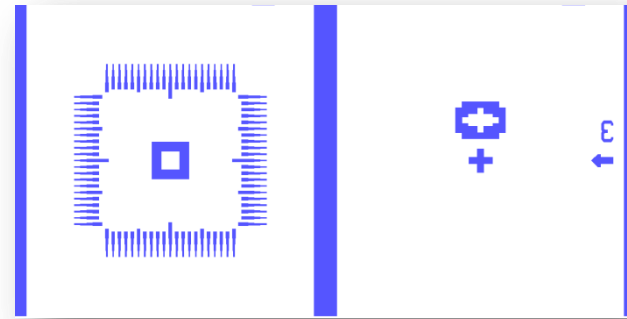


左、右藍色區塊為對準標記區域以及座標，繪圖時請勿占用，
Layout area (-3000,-3000)~(3000,3000)為使用者繪圖區，區域內由使用者自行繪製勿超界，對準標記由TSRI套製。

STD zeromark details(total 7 sets)

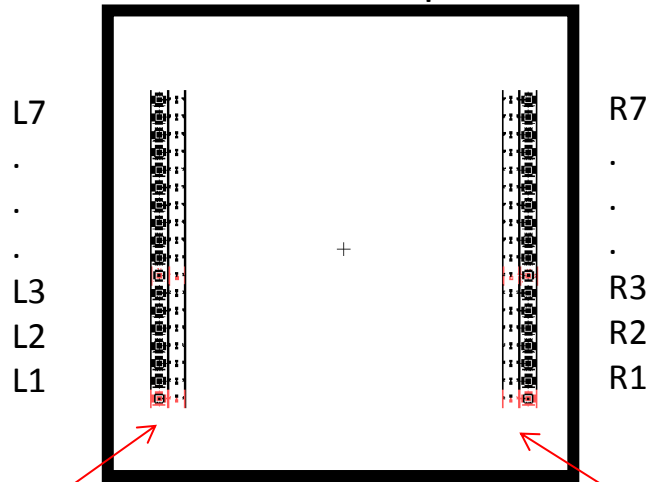


mark L3



mark R3

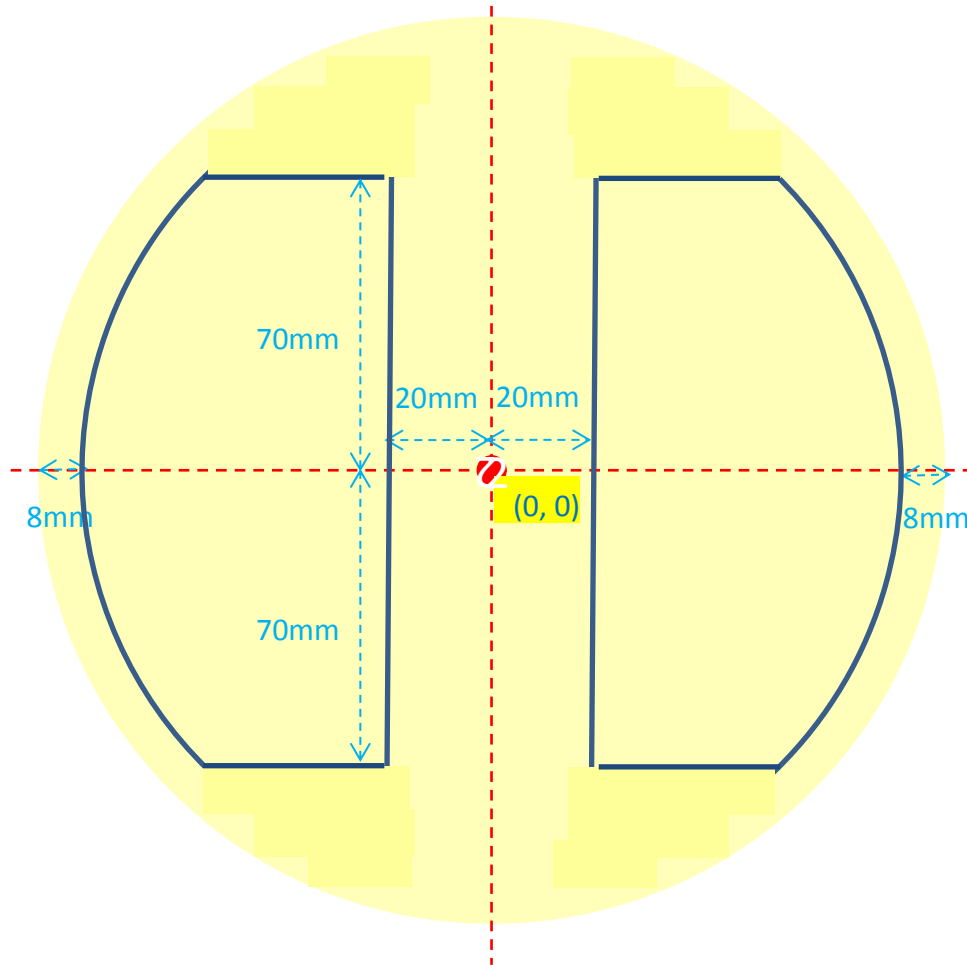
12mm chip



Left mark group

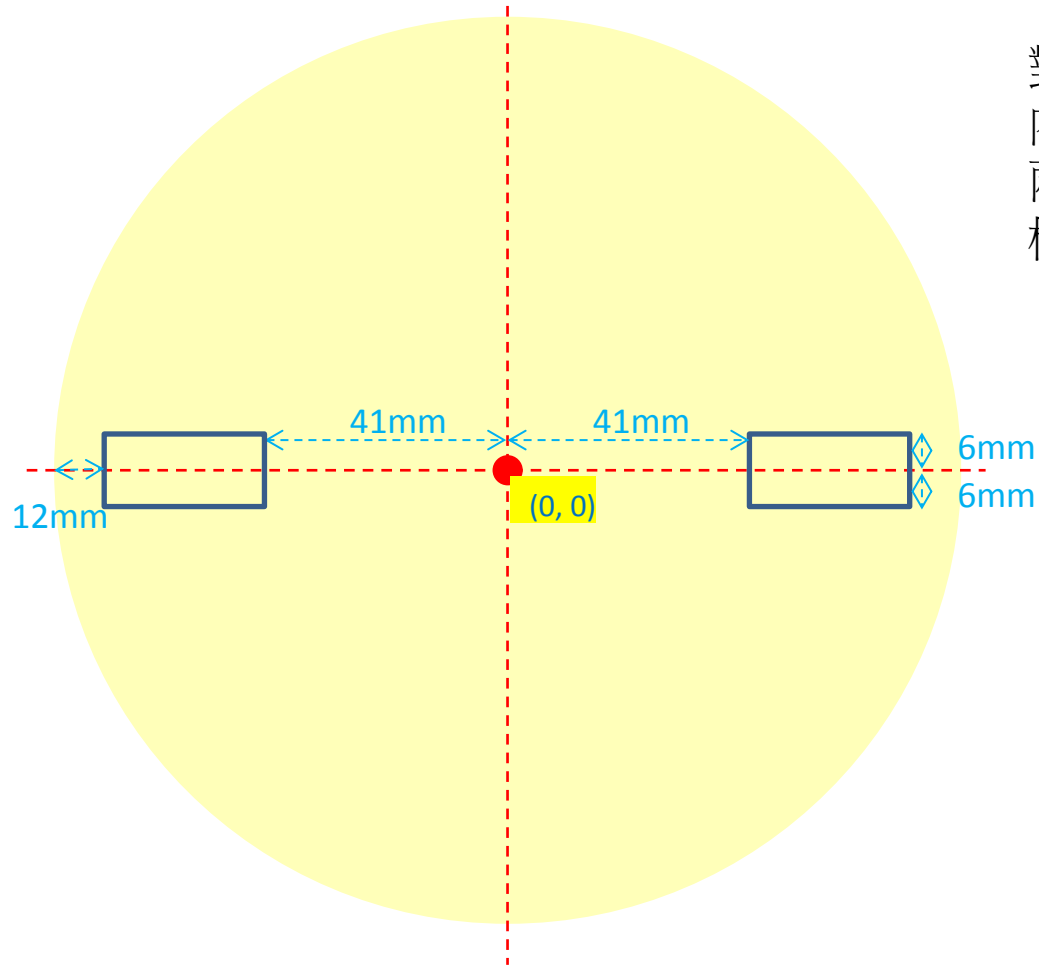
Right mark group

TSA mark position for 4" & 6" & 8" wafer(5" & 7" & 9" mask)



對準標記需位於藍色框內，兩邊各1顆為1組，兩邊對準標記須等高(Y座標相同)，方可進行正面對準。

BSA mark position for 4" & 6" & 8" wafer(5" & 7" & 9" mask)



對準標記需位於藍色框內，方可進行背面對準，兩邊對準標記須等高(Y座標相同)。

NARLabs

END